

IFN6449, IFN6450 N-Channel JFET

Features

- InterFET [N0042SY Geometry](#)
- High Voltage
- Low Input Capacitance: 3pF Maximum
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

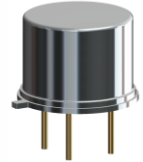
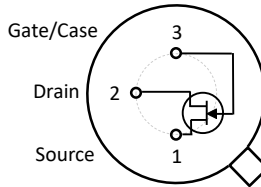
Applications

- High Voltage

Description

The -300V InterFET IFN6449 and IFN6450 are targeted for high voltage applications. The TO-39 package is hermetically sealed and suitable for military applications.

TO-39 Bottom View



Product Summary

Parameters		IFN6449 Min	IFN6450 Min	Unit
BV_{GSS}	Gate to Source Breakdown Voltage	-100	-100	V
I_{DSS}	Drain to Source Saturation Current	2	2	mA
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-2	-2	V
G_{FS}	Forward Transconductance	0.5	0.5	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFN6449; IFN6450	Through-Hole	TO-39	Bulk
IFN6449COT; IFN6450COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
IFN6449CFT; IFN6450CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

Maximum Ratings (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

Parameters	Value	Unit
V_{RGS} Reverse Gate Drain Voltage	-300; -200	V
I_{FG} Continuous Forward Gate Current	10	mA
P_D Continuous Device Power Dissipation	800	mW
P Power Derating	6.4	mW/ $^\circ\text{C}$
T_J Operating Junction Temperature	-55 to 125	$^\circ\text{C}$
T_{STG} Storage Temperature	-65 to 200	$^\circ\text{C}$

Static Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

Parameters	Conditions	IFN6449		IFN6450		Unit
		Min	Max	Min	Max	
$V_{(BR)GSS}$ Gate to Source Breakdown Voltage	$I_G = -10\mu\text{A}$, $I_D = 0\text{A}$	-100		-100		V
$V_{(BR)GDO}$ Gate Drain Breakdown Voltage	$I_G = -10\mu\text{A}$, $I_S = 0\text{A}$	-300		-200		V
I_{GSS} Gate to Source Reverse Current	$V_{GS} = -80\text{V}$, $V_{DS} = 0\text{V}$, $T_A = 25^\circ\text{C}$ $V_{GS} = -80\text{V}$, $V_{DS} = 0\text{V}$, $T_A = 150^\circ\text{C}$				-100 -100	nA μA
$V_{GS(OFF)}$ Gate to Source Cutoff Voltage	$V_{DS} = 30\text{V}$, $I_D = 4\text{nA}$	-2	-15	-2	-15	V
I_{DSS} Drain to Source Saturation Current	$V_{GS} = 0\text{V}$, $V_{DS} = 30\text{V}$ (Pulsed)	2	10	2	10	mA

Dynamic Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

Parameters	Conditions	IFN6449		IFN6450		Unit
		Min	Max	Min	Max	
G_{FS} Forward Transconductance	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{kHz}$	0.5	3	0.5	3	mS
G_{OS} Output Conductance	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{kHz}$		100		100	μS
C_{ISS} Input Capacitance	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		3		3	pF
C_{RSS} Reverse Transfer Capacitance	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		0.6		0.6	pF